SDP86XX

Optoschmitt Detector

FEATURES

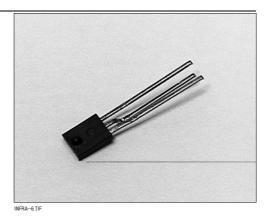
- Side-looking plastic package
- 55° (nominal) acceptance angle
- Wide sensitivity ranges
- TTL/LSTTL/CMOS compatible
- Buffer (SDP8600/8601/8602) or inverting • (SDP8610/8611/8612) logic available
- Three different lead spacing arrangements
- Mechanically and spectrally matched to • SEP8506 and SEP8706 infrared emitting diodes

DESCRIPTION

The SDP86XX series is a family of single chip Optoschmitt IC detectors molded in a side-looking black plastic package to minimize the effect of visible ambient light. The photodetector consists of a photodiode, amplifier, voltage regulator, Schmitt trigger and an NPN output transistor with a 10 k Ω (nominal) pull-up resistor. Output rise and fall times are independent of the rate of change of incident light. Detector sensitivity has been internally temperature compensated. Flexibility of use is enhanced by a choice of three different lead configurations; in-line (SDP8601/8611), 0.05 in.(1.27 mm) offset pin circle (SDP8600/8610) and 0.10 in. (2.54 mm) offset center lead (SDP8602/8612).

Device Polarity:

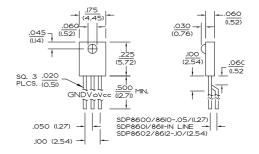
- Buffer Output is HI when incident light intensity is above the turn- on threshold level.
- Inverter Output is LO when incident light intensity is above the turn- on threshold level.



OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals

±0.005(0.12) 2 plc decimals ±0.020(0.51)



DIM 028 cdr

Honeywell

Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

200

SDP86XX

Optoschmitt Detector

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Operating Supply Voltage	Vcc	4.5		12.0	V	T _A =25°C
Turn-on Threshold Irradiance	Eet(+)				mW/cm ²	Vcc=5 V
SDP86XX-001				2.5		T _A =25°C
SDP86XX-002				1.2		(2)
SDP86XX-003				0.6		
Hysteresis (3)	HYST	5		30	%	
Supply Current	lcc				mA	Ee=0 Or 3.0 mW/cm ²
				12.0		Vcc=5 V
				15.0		Vcc=12 V
High Level Output Voltage	Vон				V	Vcc=5 V, Іон=0
SDP8600/8601/8602		2.4				Ee=3.0 mW/cm ²
SDP8610/8611/8612		2.4				Ee=0
Low Level Output Voltage	Vol				V	Vcc=5 V, IoL=12.8 mA
SDP8600/8601/8602				0.4		Ee=0
SDP8610/8611/8612				0.4		Ee=3.0 mW/cm ²
Internal Pull-Up Resistor	RINT	5.0	10.0	20.0	kΩ	
Operate Point Temperature Coefficient	Ортс		-0.76		%/°C	Emitter @ Constant
						Temperature
Output Rise Time	tr		60		ns	RL=390 Ω, CL=50 pF
Output Fall Time	tf		15		ns	RL=390 Ω, CL=50 pF
Propagation Delay, Low-High, High-Low	t _{PLH} , t _{PHL}		5.0		μs	RL=390 Ω, CL=50 pF
Clock Frequency				100	kHz	RL=390 Ω, CL=50 pF

Notes

1. It is recommended that a bypass capacitor, 0.1 µF typical, be added between Vcc and GND near the device in order to stabilize

power supply line.
2. The radiation source is an IRED with a peak wavelength of 935 nm.
3. Hysteresis is defined as the difference between the operating and release threshold intensities, expressed as a percentage of the intensities of the intensities.

18 mA

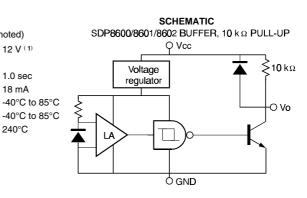
240°C

ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Supply Voltage Duration of Output Short to Vcc or Ground Output Current Operating Temperature Range Storage Temperature Range Soldering Temperature (5 sec) Notes

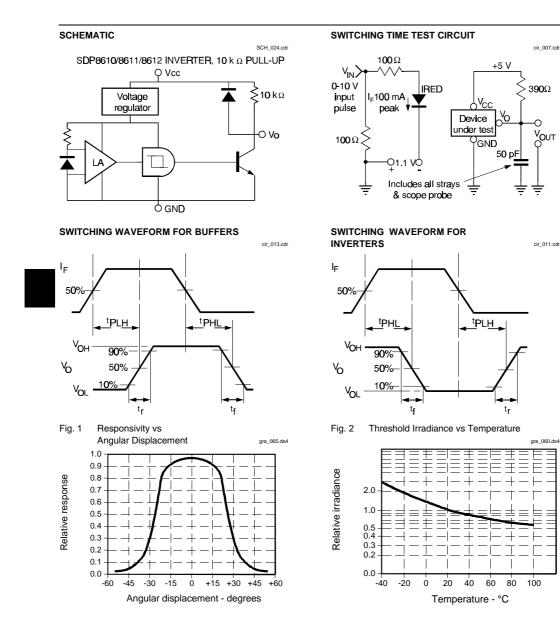
1. Derate linearly from 25°C to 5.5 V at 85°C.



Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

Honeywell

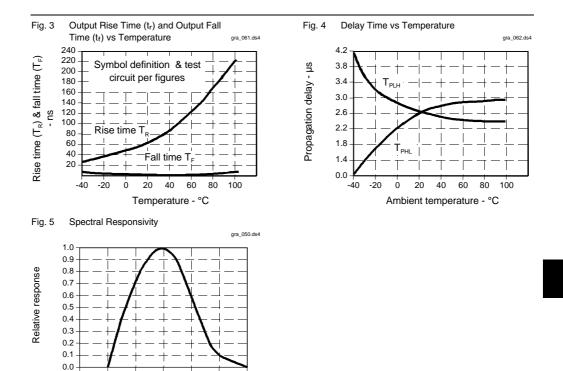




Honeywell

Honeywell reserves the right to make changes in order to improve design and supply the best products possible.





All Performance Curves Show Typical Values

800

900

Wavelength - nm

1000 1100

1200

700

600

Honeywell reserves the right to make

changes in order to improve design and supply the best products possible.

Honeywell